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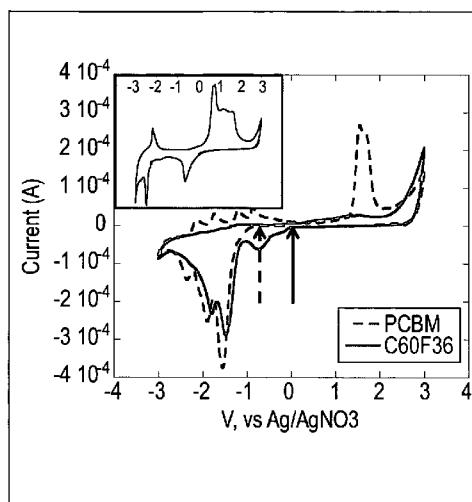


FIG. 1A

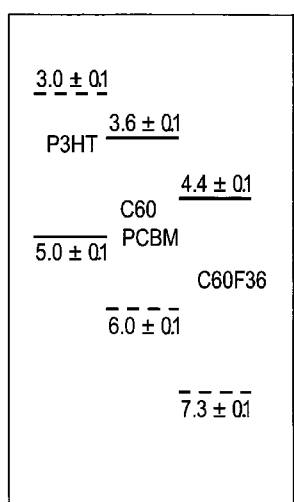


FIG. 1B

(57) **Abstract:** Methods for producing p-doped organic semiconductor material with a fullerene derivative having at least one electron-withdrawing substituent covalently attached thereto, and semiconductor compositions prepared thereby are provided. Also provided are electronic devices, such as transistors, solar-cells, illuminating devices, OLEDs and detectors, comprised of these p-doped organic semiconductor materials.

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